

Silicon NPN Power Transistors

2SD2488

DESCRIPTION

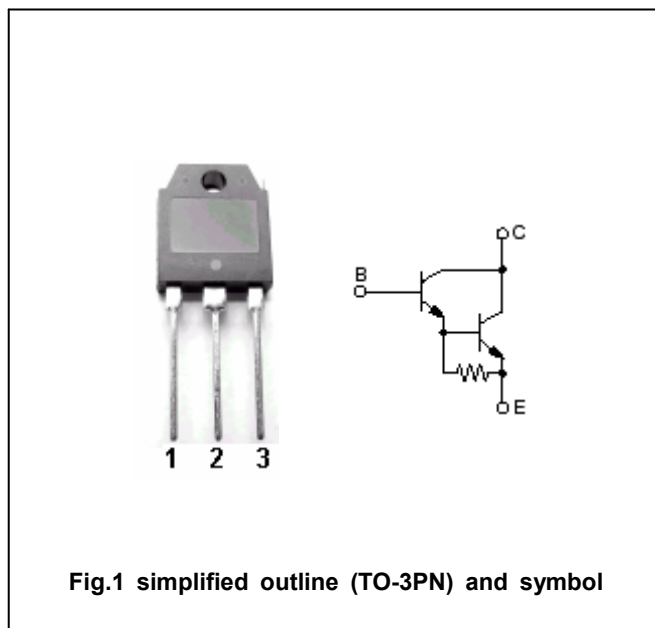
- With TO-3PN package
- DARLINGTON
- High DC current gain

APPLICATIONS

- Audio ,regulator and general purpose

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	200	V
V_{CEO}	Collector-emitter voltage	Open base	200	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		15	A
I_B	Base current		1	A
P_C	Collector power dissipation	$T_C = 25\square$	130	W
T_j	Junction temperature		150	\square
T_{stg}	Storage temperature		-55~150	\square

Silicon NPN Power Transistors**2SD2488****CHARACTERISTICS**

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=30mA ; I_B=0$	200			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=10A ; I_B=10mA$			2.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=10A ; I_B=10mA$			3.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=200V ; I_E=0$			100	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V ; I_C=0$			100	μA
h_{FE}	DC current gain	$I_C=10A ; V_{CE}=4V$	5000		30000	
C_{ob}	Output capacitance	$I_E=0 ; V_{CB}=10V ; f=1MHz$		120		pF
f_T	Transition frequency	$I_E=-2A ; V_{CE}=12V$		70		MHz

◆ **h_{FE} Classifications**

O	P	Y
5000-12000	6500-20000	15000-30000

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PACKAGE OUTLINE

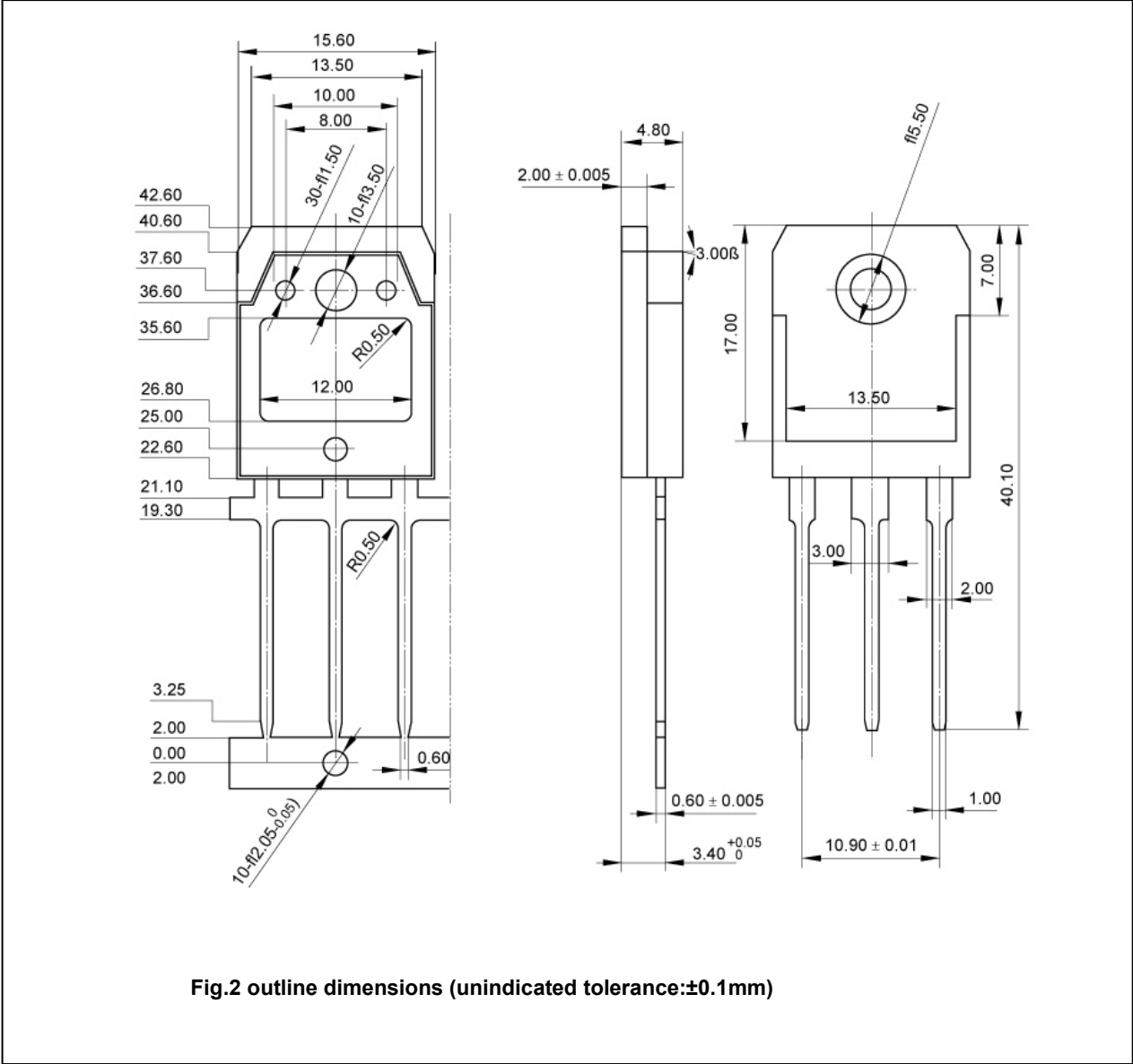


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)